

Docket No.: 503.38097CX1

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Original) A semiconductor device comprising:
  - a semiconductor substrate; and
  - a semiconductor element which comprises:
    - a first electrode provided on a front plane of said semiconductor substrate, and
    - a second electrode provided on a rear plane of said semiconductor substrate;
    - a first metallic member connected to said first electrode; and
    - a second metallic member connected to said second electrode; wherein
    - said second electrode is connected to said second metallic member via a metallic layer containing precious metal, and
    - said metallic layer is a composite metal layer comprised of a first precious metal layer provided at the front plane of said second electrode and a second precious metal layer adhered thereto by compression bonding provided at the front plane of said second metallic member.

2. (Original) A semiconductor device comprising:
  - a semiconductor chip; and
  - a metallic member connected to a chip electrode,

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wherein:

said chip electrode is composed of any of an Al film  
and an Al alloy film;  
a bonding front plane of said metallic member is  
composed of a plated precious metal film;  
said chip electrode is bonded metallically to said  
metallic member via Au bumps; and  
at least 80% of an area of a respective Au/Al  
bonding region is contacting a Au bump, said bonding region being made of an Au/Al  
alloy layer in the thickness direction.

3. (Cancelled without prejudice or disclaimer)

4. (New) A semiconductor device according to claim 1,  
wherein a surface part of said first metallic member for connecting to  
outer wirings and a surface part of said second metallic member are substantially  
positioned in a same plane.

5. (New) A semiconductor device according to claim 1,  
wherein said first electrode and said first metallic member are  
connected through plural protruding electrodes.

6. (New) A semiconductor device according to claim 1,

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said metallic layer is made of metal alloy layer having a solid phase temperature of more than 400° C and containing said precious metal as a main component.

7. (New) A semiconductor device according to claim 1,  
wherein at least one of a bump electrode made of said precious metal,  
a ball shaped electrode, a Ag particle mixed with resin, a Ag member having a  
plate shape, a sheet shape or a mesh shape or a Ag member of a plate shape  
or a sheet shape being convex/concave or having an air gap part is provided  
between a precious metallic layer positioned on said second electrode and a  
precious metallic layer positioned on said second metallic member.

8. (New) A semiconductor device according to claim 1,  
said first metallic member is connected to plural outer wirings extended  
from a part having a connecting part of said first electrode.